

GAU 1765

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July 17, 2001

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To: Commissioner of Patents and Trademarks
Washington, D.C. 20231

Fr: George O. Saile, Reg. No. 19,572
20 McIntosh Drive
Poughkeepsie, N.Y. 12603

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TC 1700

Subject:

Serial No. 09/845,480 04/30/01

S.F. Quek, T.C. Ang, Y.C. Wong,
S.Y. Long

DOUBLE-LAYERED LOW DIELECTRIC
CONSTANT DIELECTRIC DUAL DAMASCENE
METHOD

Grp. Art Unit: 1765

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
In An Application.

The following Patents and/or Publications are submitted to
comply with the duty of disclosure under CFR 1.97-1.99 and
37 CFR 1.56. Copies of each document is included herewith.

U.S. Patent 6,083,822 to Lee, "Fabrication Process for
Copper Structures", discloses a dual damascene method using a
thin silicon nitride etch stop layer.

U.S. Patent 6,025,259 to Yu et al., "Dual Damascene Process Using High Selectivity Boundary Layers", discloses a dual damascene method with etch stop layers.

In Chang et al., ULSI Technology, The McGraw Hill Companies, Inc., NY, NY, c. 1996, pp. 444-445, discusses the damascene or dual damascene process.

U.S. Patent 6,004,883 to Yu et al., "Dual Damascene Patterned Conductor Layer Formation Method Without Etch Stop Layer", discloses a dual damascene method without an etch stop layer.

U.S. Patent 6,071,809 to Zhao, "Methods for Forming High-Performing Dual-Damascene Interconnect Structures", discusses a method using an etch stop layer.

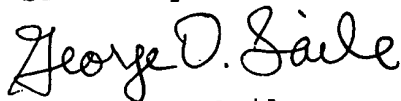
U.S. Patent 5,635,423 to Huang et al., "Simplified Dual Damascene Process for Multi-Level Metallization and Interconnection Structure", teaches various methods of forming a dual damascene opening.

U.S. Patent 5,741,626 to Jain et al., "Method for Forming a Dielectric Tantalum Nitride Layer as an Anti-reflective Coating (ARC)", discloses a dual damascene process using a tantalum nitride etch stop layer.

The following two U.S. Patents disclose a double mask self-aligned process using a silicon nitride etch sotp layer:

- 1) U.S. Patent 5,935,762 to Dai et al., "Two-Layered TSI Process for Dual Damascene Patterning".
- 2) U.S. Patent 5,877,076 to Dai, "Opposed Two-Layered Photoresist Process for Dual Damascene Patterning".

Sincerely,

A handwritten signature in cursive script that reads "George O. Saile". The signature is written in dark ink and is positioned above the printed name and registration number.

George O. Saile,
Reg. No. 19572